Docket No.: 20435/00143

CLAIMS

What is claimed as new and desired to be protected by Letters Patent of the United States is:

- 1. An aqueous slurry composition which comprises:
- A. about 0.01% by weight to about 50% by weight of abrasive particles;
 - B. about 0.01% to about 50% by weight of an oxidizer;
 - C. at least about 500 ppm of a quaternary ammonium hydroxide;
 - D. an acid having a pKa of about 2.5 or lower in an sufficient amount to provide an acidic pH; and
 - E. water.
 - 2. The composition of claim 1 wherein the amount of the abrasive particles is about 1% to about 20% by weight.
- 3. The composition of claim 1 wherein the amount of the abrasive particles is about 5% to about 15% by weight.
 - 4. The composition of claim 1 wherein the abrasive particles comprises silica particles.
 - 5. The composition of claim 1 wherein the oxidizer comprises hydrogen peroxide.
- 6. The composition of claim 1 wherein the amount of oxidizer is about 0.05 at % to 20 about 5 wt %.
 - 7. The composition of claim 1 wherein the amount of oxidizer is about 0.1 wt, % to about 1 wt. %.
 - 8. The composition of claim 1 wherein the quaternary ammonium hydroxide is represented by the formula:

 $[N R_4 R_5 R_6 R_7]$ OH

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Docket No.: 20435/00143

wherein each of R₄, R₅ R₆ and R₇ individually is an alkyl group of 1 to 20 carbon atoms.

9. The composition of claim 8 wherein the alkyl group contains 1 to 4 carbon atoms.

- 10. The composition of claim 1 wherein the quaternary ammonium hydroxide comprises tetramethyl ammonium hydroxide or tetrabutyl ammonium hydroxide.
- 5 11. The composition of claim 1 wherein the amount of quaternary ammonium hydroxide is about 1000 ppm or higher.
 - 12. The composition of claim 1 wherein the amount of quaternary ammonium hydroxide is about 2500 ppm or higher.
 - 13. The composition of claim 1 wherein the acid comprises phosphoric acid.
 - 14. The composition of claim 1 wherein the pH is at least about 1.5.

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- 15. The composition of claim 1 wherein the pH is about 1.5 to about 5.
- 16. The composition of claim 1 wherein the pH is at least about 2.
- 17. The composition of claim 1 which further comprises a corrosion inhibitor.
- 18. The composition of claim 16 wherein the corrosion inhibitor comprises benzotriazole.
 - 19. The composition of claim 1 which further comprises a surface active agent.
 - 20. A method for polishing a metal which comprises providing on the metal an aqueous slurry composition comprising:
 - A. about 0.1% by weight to about 50% by weight of abrasive particles;
 - B. about 0.1% to about 50% by weight of an oxidizer;
 - C. at least about 500 ppm of a quaternary ammonium hydroxide;
 - D. an acid being a pKa of about 2.5 or lower in amount to provide an acidic pH;

Docket No.: 20435/00143

and E. water;

and contacting the metal with a polishing pad.

21. A process for fabricating semiconductor integrated circuit structure comprising: forming circuits on the surface of a semiconductor wafer by photolithographic process; planarizing the surface by chemical mechanical polishing with the composition of claim 1.

22. The process of claim 21 wherein the integrated circuit structure comprise a semiconductor substrate; a ferromagnetic metal layer; a metal selected from the group consisting of group 3d and 5d of the periodic table; a layer of copper or aluminum; a barrier layer; and a dielectric layer.

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